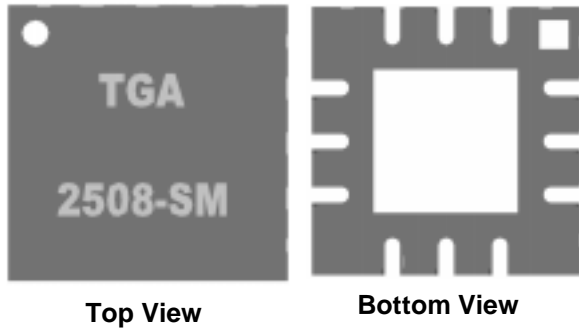


**Ku-Band VSAT Packaged Amplifier**

**TGA2508-EPU-SM**

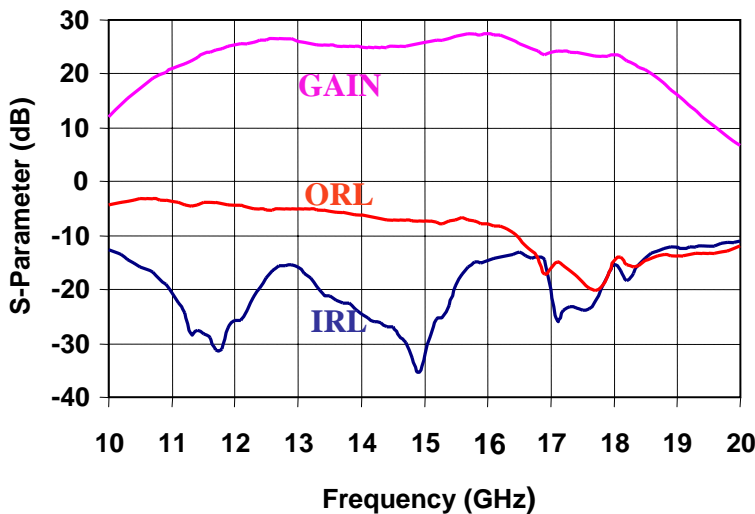


**Key Features**

- Typical Frequency Range: 12 - 19 GHz
- 25 dB Nominal Gain
- 29 dBm Nominal P1dB
- Bias Conditions: 7 V, 433 mA
- PHEMT Technology
- Low cost true surface mount package
- Package Dimensions:  
4.0 x 4.0 x 0.9 mm  
(0.157 x 0.157 x 0.035 in)

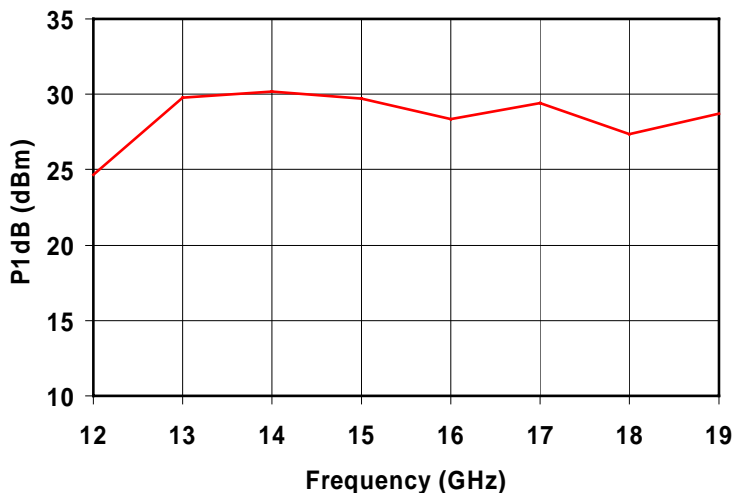
**Preliminary Measured Data**

Bias Conditions:  $V_d = 7\text{ V}$ ,  $I_d = 433\text{ mA}$



**Primary Applications**

- VSAT Ground Terminals
- Point to Point Radio
- Military Ku Band
- Ku-Band Space



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

TABLE I  
MAXIMUM RATINGS 5/

SYMBOL	PARAMETER	VALUE	NOTES
V <sup>+</sup>	Positive Supply Voltage	8 V	<u>4/</u>
V <sup>-</sup>	Negative Supply Voltage Range	-2 to 0 V	
I <sup>+</sup>	Positive Supply Current (Quiescent)	591 mA	<u>4/</u>
I <sub>G</sub>	Gate Supply Current	16 mA	
P <sub>IN</sub>	Input Continuous Wave Power	17 dBm	
P <sub>D</sub>	Power Dissipation	4.7 W	<u>3/ 4/</u>
T <sub>CH</sub>	Operating Channel Temperature	150 °C	<u>1/ 2/</u>
T <sub>M</sub>	Mounting Temperature (30 Seconds)	250 °C	
T <sub>STG</sub>	Storage Temperature	-65 to 150 °C	
T <sub>CASE</sub>	Package Operating Temperature	-40 to 110 °C	

- 1/ These ratings apply to each individual FET.
- 2/ Junction operating temperature will directly affect the device median time to failure (T<sub>M</sub>). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.
- 3/ When operated at this bias condition with a base plate temperature of 70 °C, the median life is 4.3E+6 hrs.
- 4/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P<sub>D</sub>.
- 5/ These ratings represent the maximum operable values for this device.

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**TABLE II**  
**ELECTRICAL CHARACTERISTICS**

(Ta = 25°C ± 5°C)

PARAMETER	TYPICAL	UNITS
Frequency Range	12 - 19	GHz
Drain Operating	7	V
Quiescent Current	433	mA
Small Signal Gain	25	dB
Input Return Loss (Linear Small Signal)	15	dB
Output Return Loss (Linear Small Signal)	7	dB
Output Power @ 1 dB Compression Gain	29	dBm

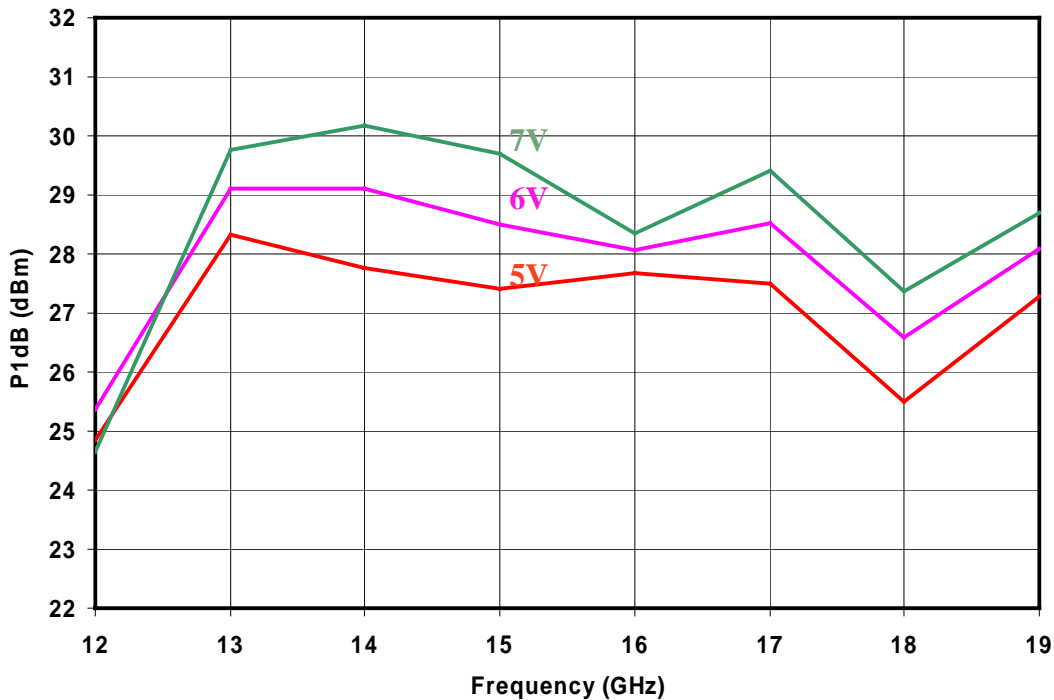
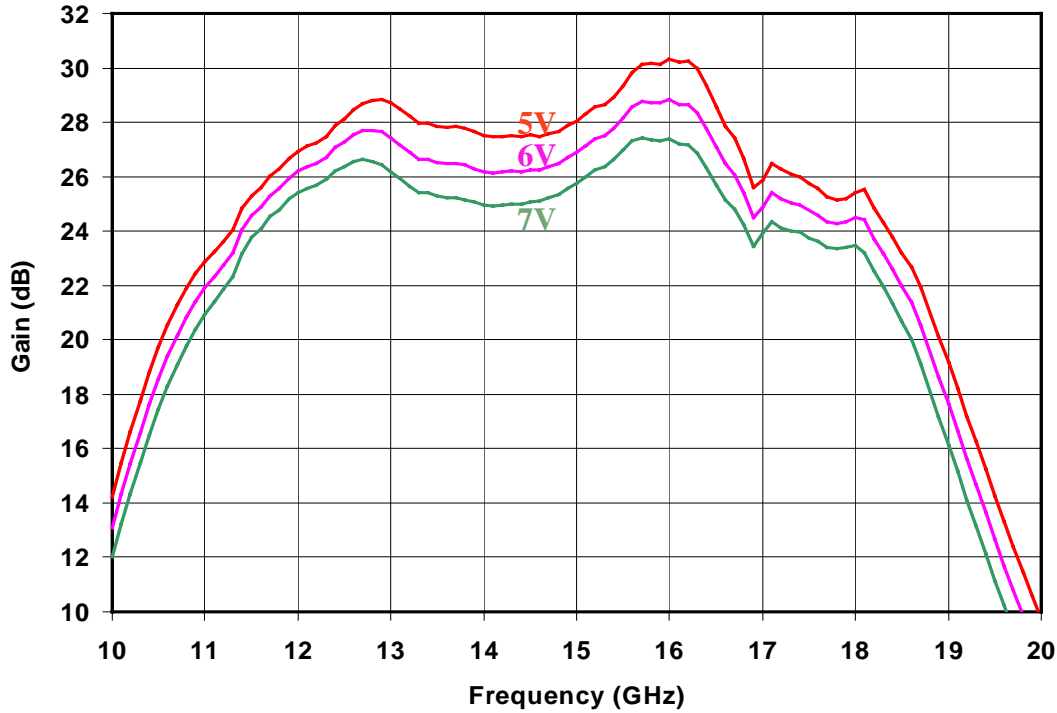
**TABLE III**  
**THERMAL INFORMATION**

PARAMETER	TEST CONDITIONS	T <sub>CH</sub> (°C)	R <sub>θJC</sub> (°C/W)	T <sub>M</sub> (HRS)
R <sub>θJC</sub> Thermal Resistance (Channel to Case)	Vd = 7 V I <sub>D</sub> = 433 mA Pdiss = 3.031 W	111	13.5	3.8 E+7

Note: Worst case condition with no RF applied, 100% of DC power is dissipated, Case Temperature @ 70 °C

**Preliminary Measured Data**

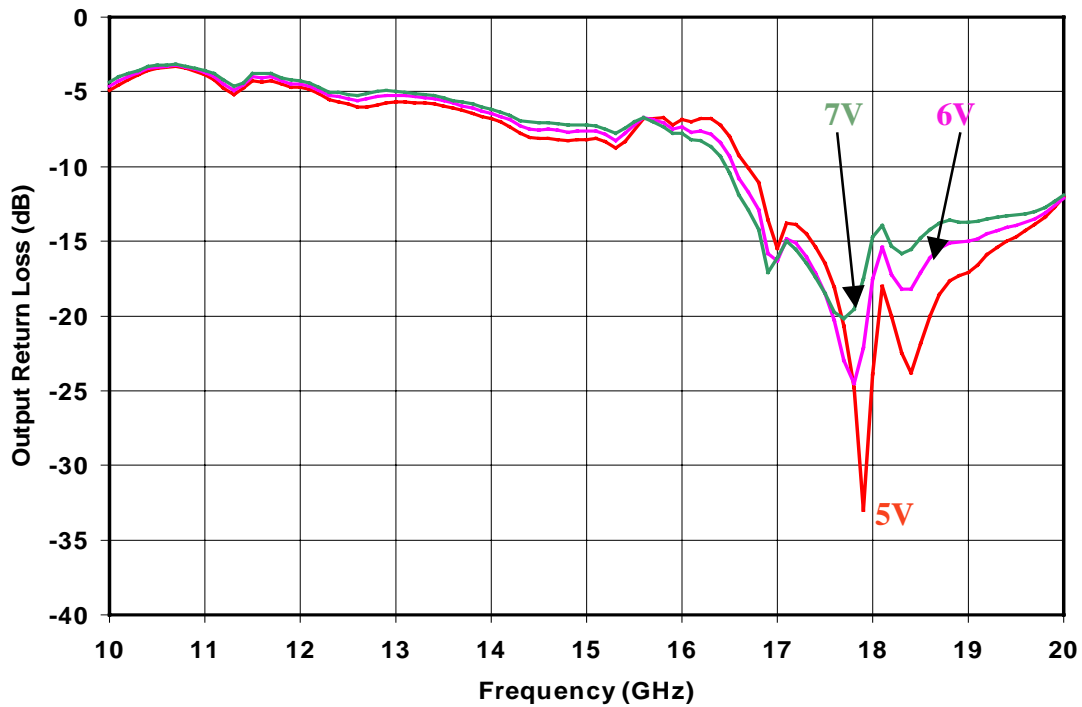
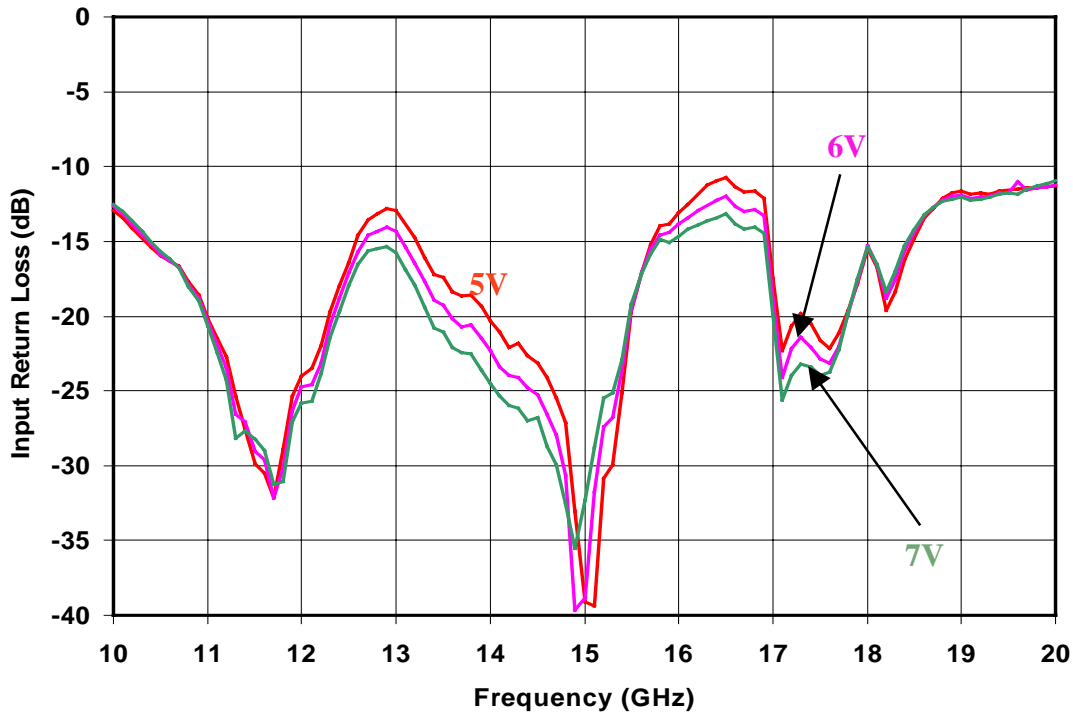
Bias Conditions:  $V_d = 5 - 7 \text{ V}$ ,  $I_d = 433 \text{ mA}$



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

### Preliminary Measured Data

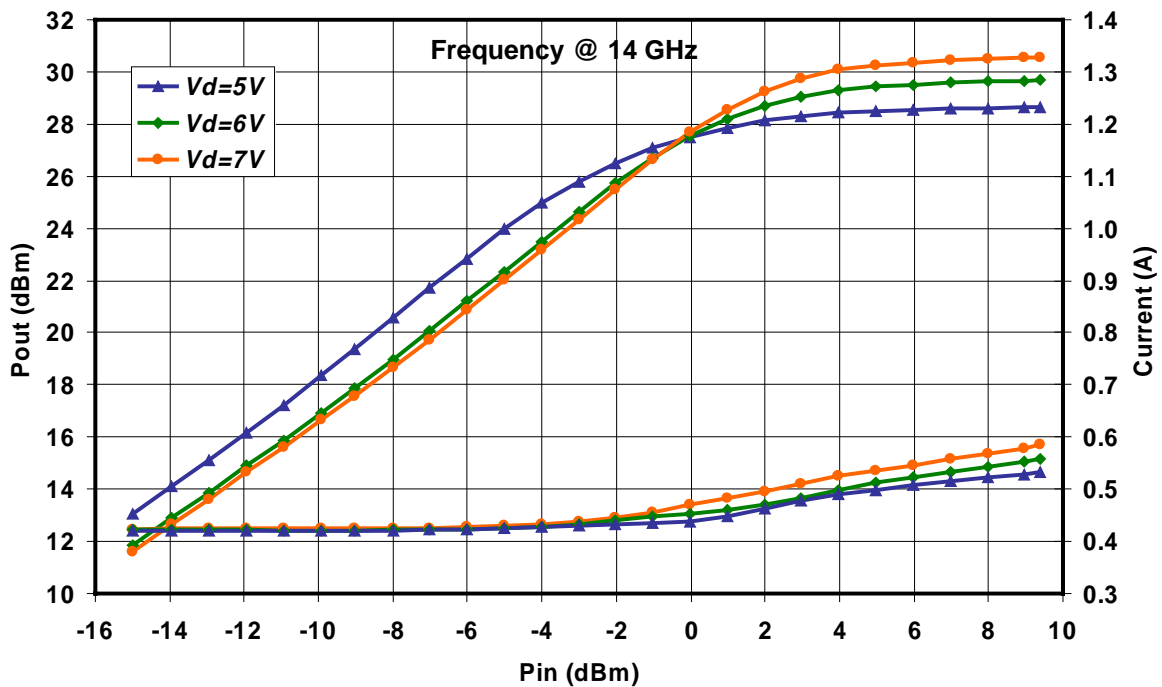
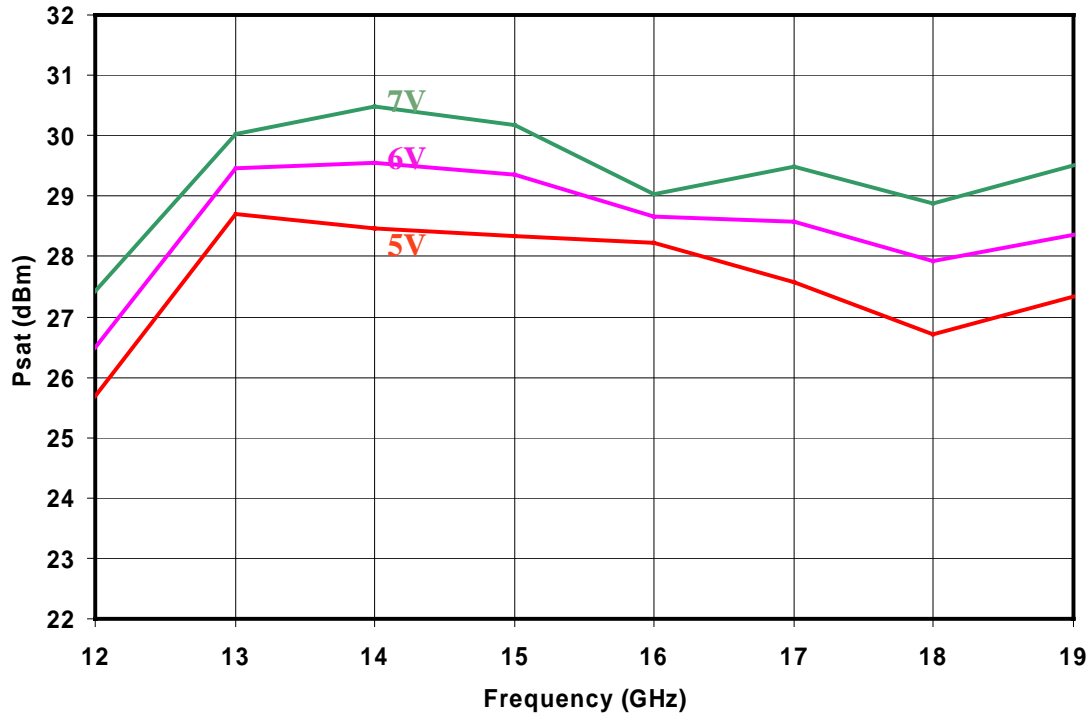
Bias Conditions:  $V_d = 5 - 7 \text{ V}$ ,  $I_d = 433 \text{ mA}$



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

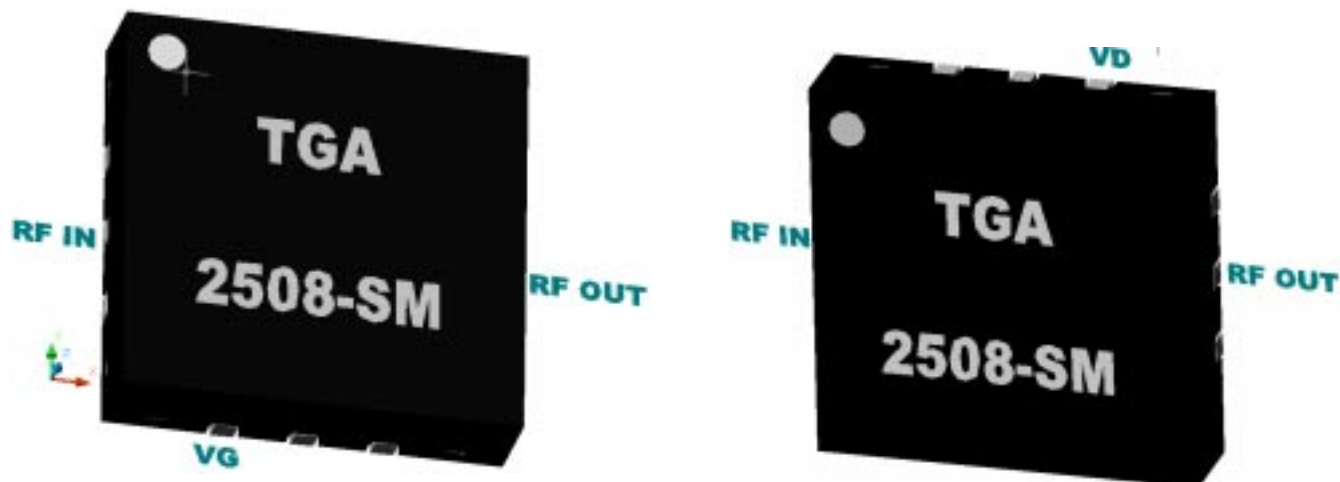
**Preliminary Measured Data**

Bias Conditions:  $V_d = 5 - 7 \text{ V}$ ,  $I_d = 433 \text{ mA}$

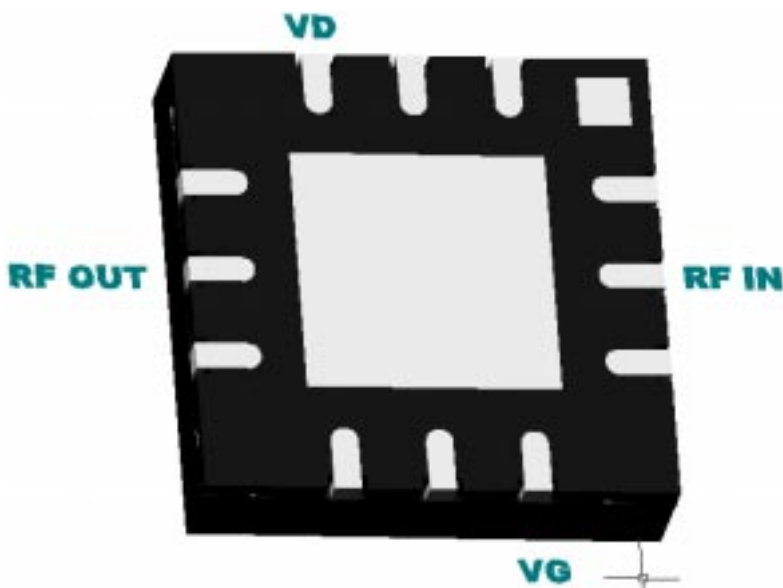


Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

## Package Layout



Top View

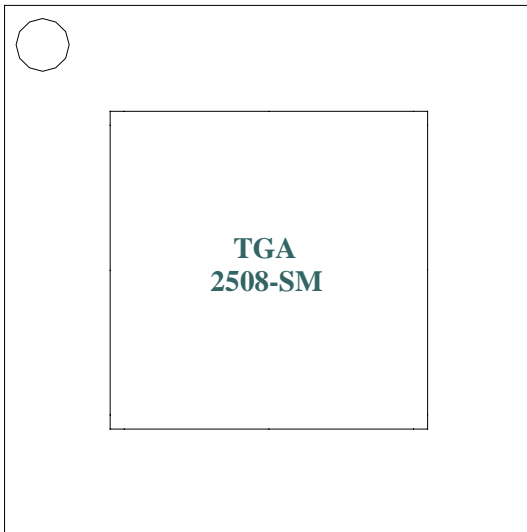


Bottom View

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

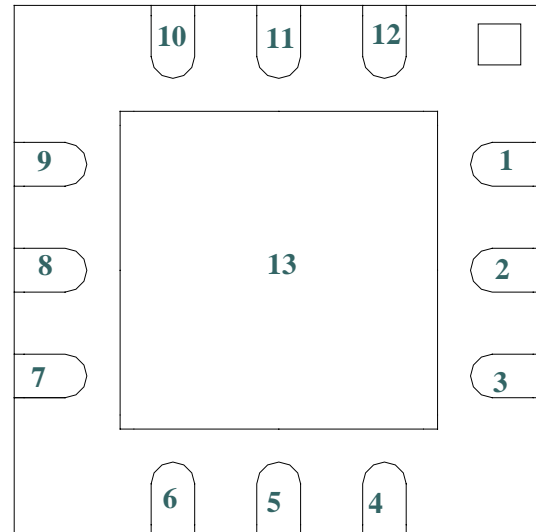
*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice*

**Package Pinout Diagram**



**Top Side**

Dot indicates Pin 1



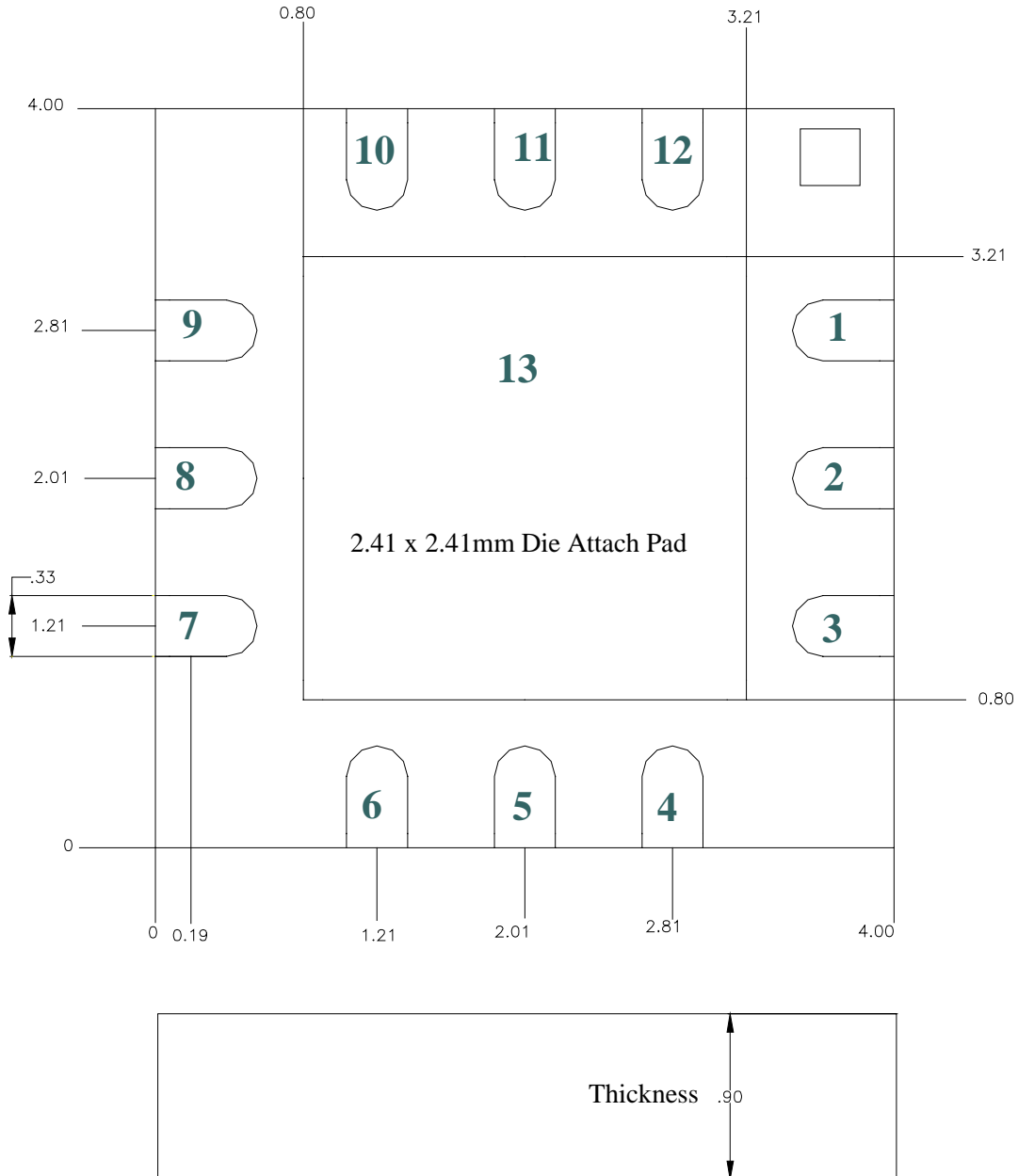
**Bottom Side**

Pin	Description
1	NC
2	RF Input
3	NC
4	Vg
5 - 7	NC
8	RF Output
9	NC
10	Vd
11, 12	NC
13	GND

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice*



**Mechanical Drawing  
(Bottom Side)**



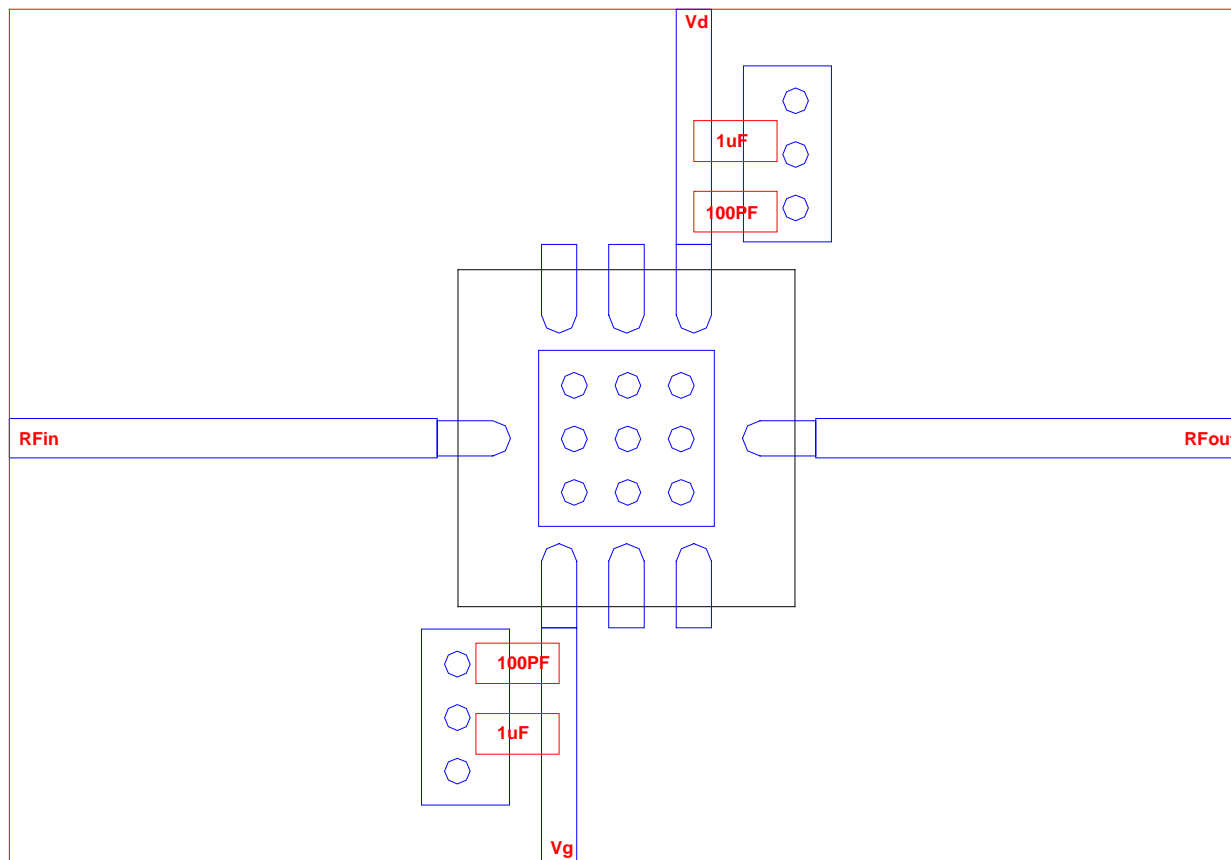
**Units: Millimeters**

**Package tolerance: +/- 0.10**

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice*

## Recommended Board Layout Assembly



All measurement was made with part solder to 0.008 in thick of RO4003

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[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.